

PATENT  
8075-1007

## IN THE U.S. PATENT AND TRADEMARK OFFICE



In re application of

Rikizo HATAKEYAMA et al.

Conf. Unknown

Application No. 10/528,561 ✓

Group Unknown

Filed March 21, 2005

METHOD FOR PRODUCING ENDOHEDRAL  
FULLERENES AND DEVICE THEREFORINFORMATION DISCLOSURE STATEMENTCommissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

June 21, 2005

Sir:

In compliance with Rules 1.97 and 1.98, and in fulfillment of the duty of disclosure under Rule 1.56, the cited documents are made of record on the enclosed PTO Form-1449.

A concise explanation of the relevance of these items is that these references were cited in the corresponding International Application Serial No. PCT/JP03/12098, filed September 22, 2003.

Respectfully submitted,

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RJP/mjr  
June 21, 2005

(Use several sheets if necessary)

Application No.:  
**10/528,561**

Applicant:  
**HATAKEYAMA et al.**

Filing Date:  
**March 21, 2005**

Group Art Unit:  
**Unknown**

## U.S. PATENT DOCUMENTS

[illegible]

**FOREIGN PATENT DOCUMENTS**

[illegible]

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

Hatakeyama, R. et al., "Characteristics and Applications of Fullerene Plasmas", 6 Fullerenes Plasma no Seishitsu to Oyo", Journal of Plasma and Fusion Research, 1999, Vol. 75, No. 8, pp. 927-933.

Hatakeyama, R. et al., "Formation of Alkali-and Si-Endohedral Fullerenes Based on Plasma Technology, Electrochemical Society Proceedings, 2001, Vol. 2001-11, pp. 341-348.

Hirata et al., "The K<sup>+</sup>-C<sub>60</sub>-plasma for material processing, Plasma Sources Sci. Technol., 1996, Vol. 5, No. 2, pp. 282-292.

EXAMINER:

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

\* English language abstract provided for the Examiner's convenience